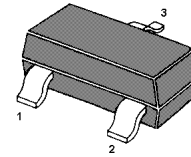
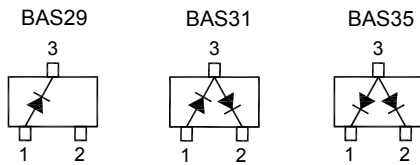


BAS29, BAS31, BAS35

Silicon Epitaxial Planar Switching Diodes



BAS29 Marking Code: **L20**
 BAS31 Marking Code: **L21**
 BAS35 Marking Code: **L22**
 SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	120	V
Maximum Average Forward Current	$I_{F(AV)}$	200	mA
Repetitive Peak Forward Current	I_{FRM}	600	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	2 1	A
	$t = 1\ \mu\text{s}$ $t = 1\ \text{s}$		
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage				
at $I_F = 10\ \text{mA}$	V_F	-	750	mV
at $I_F = 50\ \text{mA}$	V_F	-	840	mV
at $I_F = 100\ \text{mA}$	V_F	-	900	mV
at $I_F = 200\ \text{mA}$	V_F	-	1	V
at $I_F = 400\ \text{mA}$	V_F	-	1.25	V
Reverse Current				
at $V_R = 90\ \text{V}$	I_R	-	100	nA
at $V_R = 90\ \text{V}, T_J = 150\text{ }^\circ\text{C}$	I_R	-	100	μA
Reverse Breakdown Voltage	$V_{(BR)R}$	120	-	V
at $I_R = 1\ \text{mA}$				
Total Capacitance	C_T	-	35	pF
at $V_R = 0\ \text{V}, f = 1\ \text{MHz}$				
Reverse Recovery Time	t_{rr}	-	50	ns
at $I_F = I_R = 10\ \text{mA}, I_{rr} = 1\ \text{mA}, R_L = 100\ \Omega$				

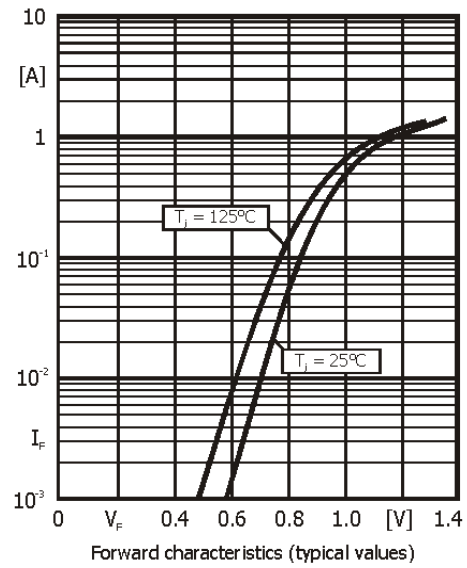
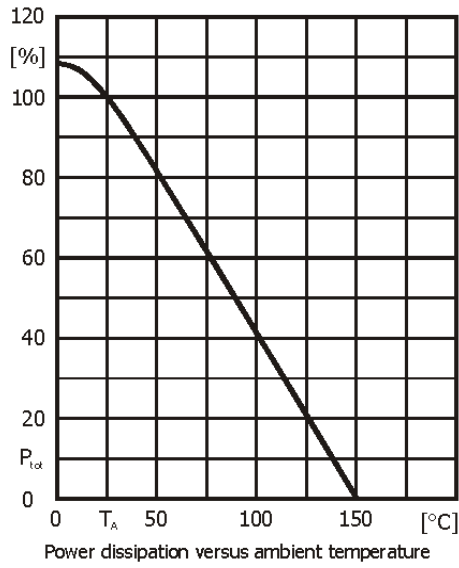
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ISO14001 : 2004 Certificate No. 121509007
 ISO 9001 : 2008 Certificate No. 50114012
 OHSAS 18001 : 2007 Certificate No. 0513150006
 IECQ QC 080000 Certificate No. E0241000741002

Dated : 21/10/2012

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